

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

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LIST OF REFERENCES CITED BY APPLICANT

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FOREIGN PATENT DOCUMENTS DOCUMENT SUB-TRANSLATION NO. DATE COUNTRY **CLASS** YES NO PART. 10-256662 09/10/98 **JAPAN** MOV AΑ AΒ AC

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

Nakamura, Shuji, "High-Power Ga P-N Junction Blue Light Emitting Diodes" 12/91 Japanese Journal Vol. 30, No.12A pp.L 1998-L 2001 AD MOU ΑE Polian, Grimsditch, and Grezegory, "Elastic Constraints of gallium nitride" 04/15/96, J.App.Phys.,Vol.79,No.6 MOU G.H. Olsen and M. Ettenburg, "Calculated stresses in multilayered heteroepitaxial structures" 06/77, Journal of Applied Physics, Vol.48, No.6 AF MOV Hiramatsu, Detchprohm, and Akasaski, "Relaxation Nechanism of Thermal Stresses in the Heterostructure of GaN Grown on Sapphire by Vapor Phase Epitaxy" 04/93, jon. J. Appl. Phys. Vol.23 Part 1, No.4 pp.1528-1533 mo J AG Bernstein, "Elastic Constants of Synthetic Sapphire at 27oC" 01/63, Journal of Applied Physics Vol.34, No. 1 pp.169-172 MOU AΗ Αl

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